



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16512Generic Copy

Issue Date: 12-Aug-2010**TITLE:** Qualification of Additional Fab and Assembly Source for CM1213A-04SO, CM1293A-04SO**PROPOSED FIRST SHIP DATE:** 12-Nov-2010**AFFECTED CHANGE CATEGORY(S):** Fab Site Change; Package Change; Assembly Site Change**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**Contact your local ON Semiconductor Sales Office or Jill Daugherty <jill.daugherty@onsemi.com>**SAMPLES:** Contact your local ON Semiconductor Sales Office**ADDITIONAL RELIABILITY DATA:** AvailableContact your local ON Semiconductor Sales Office or Laura Rivers <laura.rivers@onsemi.com>**NOTIFICATION TYPE:**

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.**DESCRIPTION AND PURPOSE:**

This is the final notification announcing that ON Semiconductor is qualifying an additional wafer source and an additional assembly site for CM1213A-04SO and CM1293A-04SO products. The additional wafer source will be ON Semiconductor's qualified Low Capacitance TVS process sourced from the ON Semiconductor COM1 Fab in Phoenix, US and the ON Semiconductor FAB2 in Oudenaarde, Belgium. The additional assembly site will be the Leshan assembly facility in Leshan, China, which is a joint venture between ON Semiconductor and Leshan Radio Company LTD.

The purpose of this change is to qualify a second product source in order to ensure continuous delivery of product to the customer.

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16512**Datasheet changes:

1. The Diode Forward Voltage (VF) specification will be changed in the following ways:
 - a. The min and max VF spec will be removed
 - b. The typ spec will be changed from 0.8V to 0.9V
 - c. The "Top Diode" and "Bottom Diode" differentiators will be removed
2. The Channel Input Capacitance (Cin) condition specified on the datasheet will be modified to match updated testing procedures: the Cin will be specified at Vin = 0V and freq = 1 MHz. This testing condition is more rigorous than the current capacitance test specification.

Marking change:

CM1213A-04SO: marking will change from "D234" to "234"

CM1293A-04SO: marking will change from "D635" to "635"

Additional changes:

1. The current CM1213A-04SO and CM1293A-04SO product uses Au wire. The product from the Leshan facility will use Cu wire.
2. The current package uses an epoxy die attach process. The product from the Leshan facility will use a eutectic die attach process.
3. The case outline for the two devices will be modified slightly to accommodate product from either assembly site.



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RELIABILITY DATA SUMMARY:

Test:	Conditions:	Interval:	Results
HTRB	TA=150C, 80% Rated Voltage	1008 hrs	0/252
Precondition	MSL1 @ 260C , 3 X IR at 260 C		0/1008
Autoclave+PC	Ta=121C RH=100% ~15 psig	96 hrs	0/252
H3TRB+PC	Ta=85C RH=85% bias=80% rated V 100V Max	1008 hrs	0/252
IOL+PC	Ta=25C, Delta TJ = 100 C, Ton/off = 2 min.	15000 cyc	0/252
TC+PC	Ta= -65 C to 150 C	1000 cyc	0/252
DPA Per AECQ101, after 1000 cyc TC			0/6
DPA Per AECQ101, after 1008 hrs H3TRB			0/6
RSH	Ta=260C, 10 sec dwell		0/30

ELECTRICAL CHARACTERISTIC SUMMARY:

Available upon request.

CHANGED PART IDENTIFICATION:

Devices with date code marking of Y or later may be sourced from either factory.



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List of affected General Parts:

CM1213A-04SO
CM1293A-04SO